F	2018-7				
G	2019-11-30	2	上限由原来的 改为		
H	2022-7-9	2 3	庞隆基申请 上限由原来的 改为 （典型值 改成 ），更新曲线图		

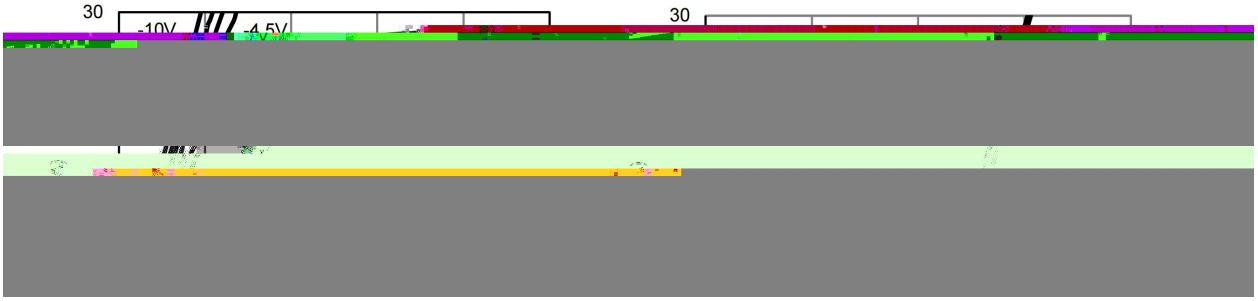
TO-220 P MOS

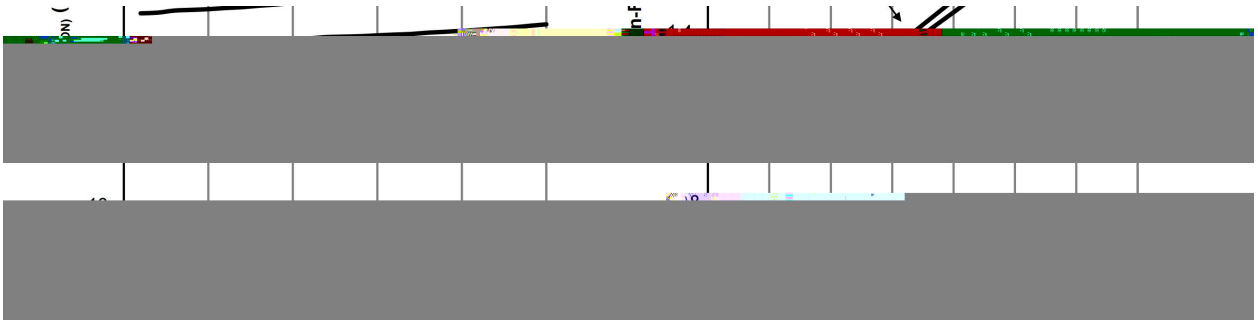
P-CHANNEL MOSFET in a TO-220 Plastic Package.

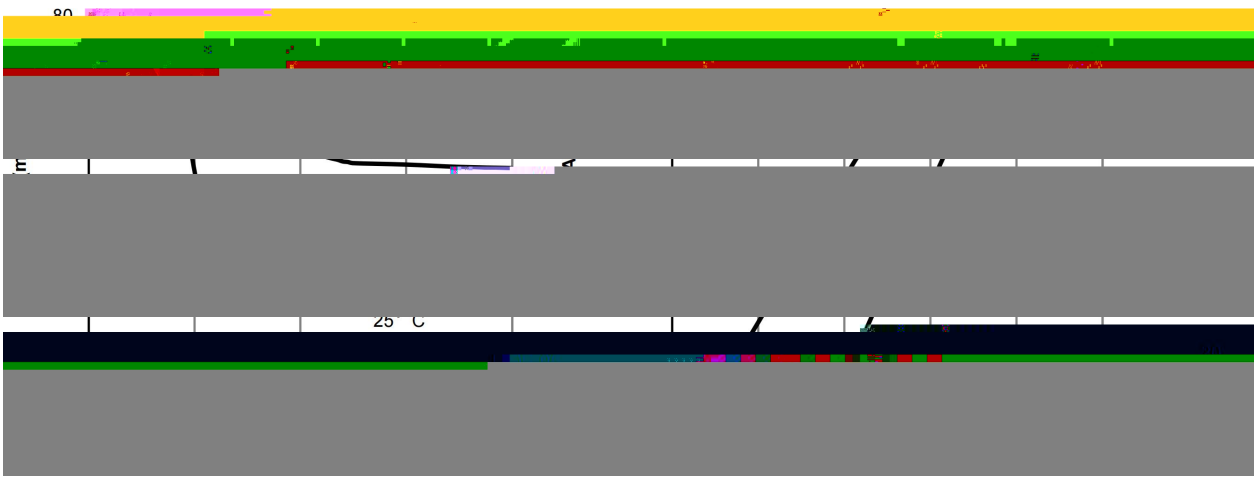
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-60	V
Drain Current		I_D(Tc=25℃)	-50	A
Drain Current - Pulsed		I_{DM}	-200	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D(Tc=25℃)	118	W
Single Pulsed Avalanche Energy		E_{AS}	250	mJ
Avalanche Current(L=0.5mH)		I_{AS}	25	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	
Thermal resistance, junction - ambient	t ≤ 10s	$R_{\theta JA}$	15	℃/ W
	Steady-State		60	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	1.1	

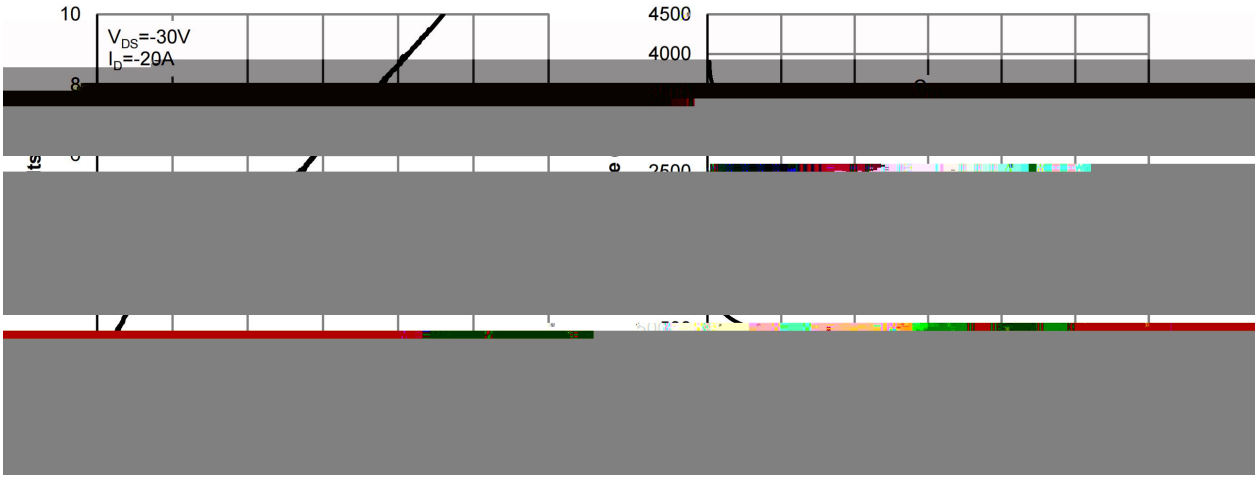
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-60	-68		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V V_{GS}=0V			-1.0	μA
		V_{DS}=-48V T_C=150℃			-10	
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±0.1	μA
Gate Threshold Voltage	[redacted]	V_{DS}=V_{GS} I_D=-250μA	-1	-1.6	-3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V I_D=-20A		30	35	mΩ
	$R_{DS(on)}$	V_{GS}=-4.5V I_D=-10A		40	45	mΩ
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=-1A			-1.2	V
Gate resistance	Rg			10		Ω
Input Capacitance	C_{iss}	V_{DS}=-25V V_{GS}=0V f=1.0MHz		3200		pF
Output Capacitance	C_{oss}			800		pF

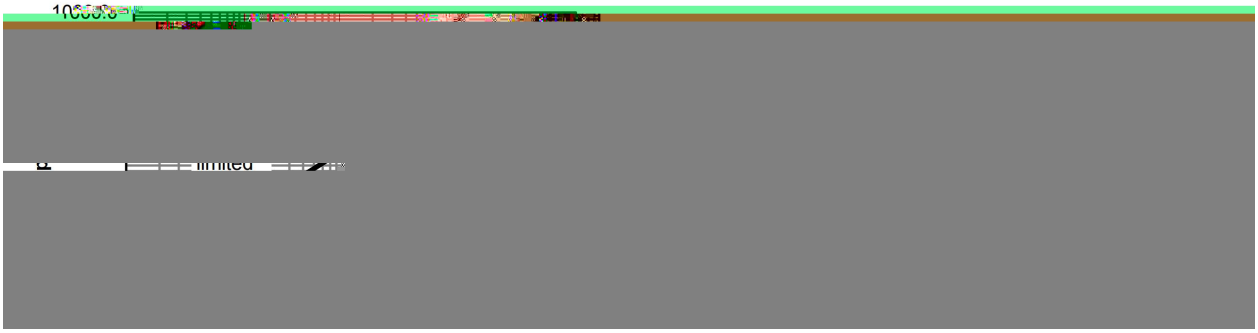
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=-10V V_{DS}=-30V R_L=1.5 R_{GEN}=3 Ω		12		ns
Turn-On Rise Time	t_r			14.5		
Turn-Off Delay Time	$t_{d(off)}$			38		
Turn-Off Fall Time	t_f			15		


30
-10V
-4.5V
30




80
25°C


10
V_{DS}=-30V
I_D=-20A
8
4500
4000
2500


limited


10


Min
Max
Min
Max
9.8
10.2
1.2
1.4
15.7
16.1
9.0
9.4